# DISCRETE SEMICONDUCTORS

# DATA SHEET

**PEMH11; PUMH11** NPN/NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

Product specification Supersedes data of 2001 Oct 22 2003 Oct 20





# NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

PEMH11; PUMH11

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

## **APPLICATIONS**

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- . Control of IC inputs.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	_	50	V
I <sub>O</sub>	output current (DC)	_	100	mA
TR1	NPN	_	_	_
TR2	NPN	_	_	_
R1	bias resistor	10	-	kΩ
R2	bias resistor	10	_	kΩ

#### **DESCRIPTION**

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### PRODUCT OVERVIEW

TYPE	PACE	KAGE	MARKING CODE	PNP/PNP	NPN/PNP
NUMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMH11	SOT666		H1	PEMB11	PEMD3
PUMH11	SOT363	SC-88	H*1 <sup>(1)</sup>	PUMB11	PUMD3

## Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

## SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING
I TPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION
PEMH11	6 5 4	1	emitter TR1
PUMH11	6 5 4	2	base TR1
	R1 R2 TR2 TR2	3	collector TR2
		4	emitter TR2
		5	base TR2
		6	collector TR1
	1 2 3		
	1 2 3 Top view MHC650		
	10p view MHC650		

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## **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
I TPE NUMBER	NAME	DESCRIPTION	VERSION
PEMH11	_	plastic surface mounted package; 6 leads	SOT666
PUMH11	<ul> <li>plastic surface mounted package; 6 leads</li> </ul>		SOT363

## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	or		-		
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+40	V
	negative		_	-10	V
Io	output current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	_	300	mW

## **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or		•	
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Per transis	Per transistor							
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	_	_	100	nA		
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	_	_	1	μΑ		
		V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C	_	_	50	μΑ		
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	_	_	400	μΑ		
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	30	_	_			
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV		
$V_{i(off)}$	input-off voltage	$I_C = 100 \mu\text{A};  V_{CE} = 5 \text{V}$	_	1.1	0.8	V		
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 0.3 V	_	1.8	_	V		
R1	input resistor		7	10	13	kΩ		
R2 R1	resistor ratio		0.8	1	1.2			
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	2.5	pF		

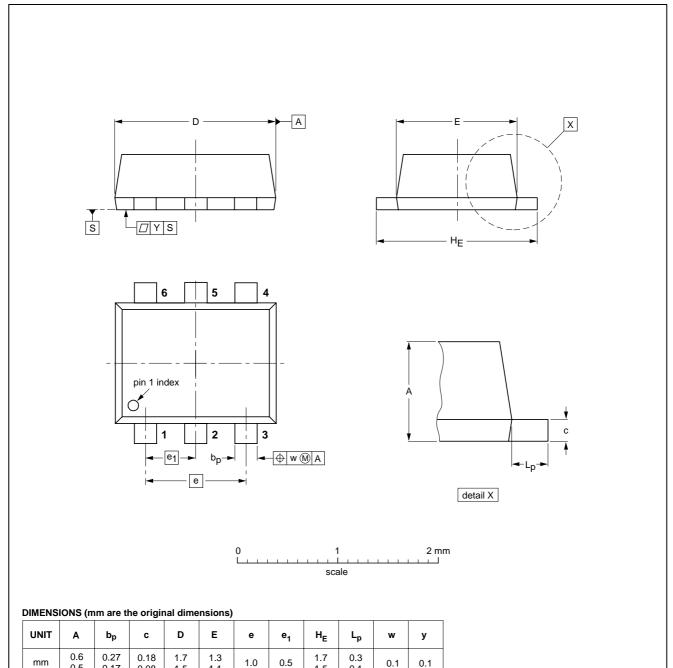
# NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

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## **PACKAGE OUTLINES**

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						<del>-01-01-04</del> 01-08-27

2003 Oct 20 5

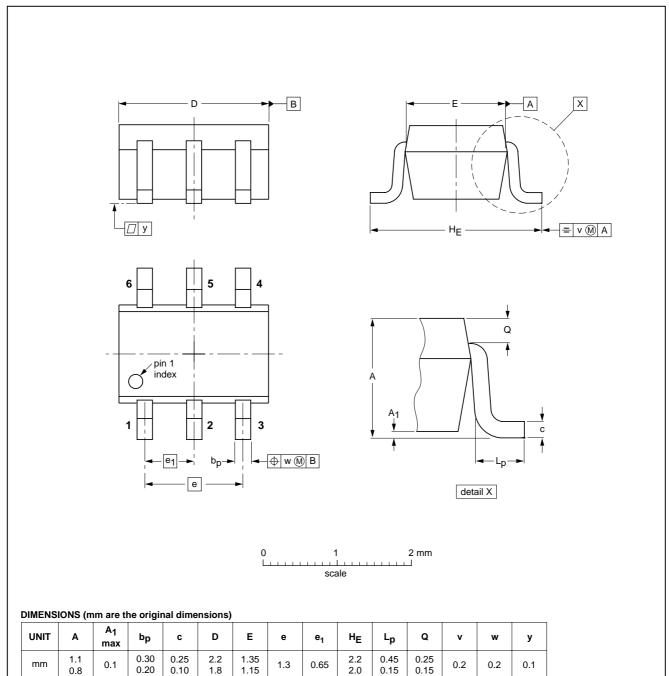
0.17

# NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

# PEMH11; PUMH11

## Plastic surface mounted package; 6 leads

**SOT363** 



OUTLINE	REFERENCES			REFERENCES		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

# NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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